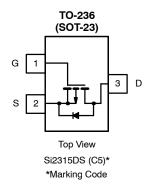


P-Channel 1.25-W, 1.8-V (G-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}\left(\Omega\right)$	I _D (A)	
	0.055 @ V _{GS} = -4.5 V	±3.5	
-12	0.075 @ V _{GS} = -2.5 V	±3	
	0.118 @ V _{GS} = -1.8 V	±2	





Ordering Information: Si2315DS-T1

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	-12	.,	
Gate-Source Voltage		V _{GS}	±8		
Continuous Drain Current (T, = 150°C)a, b	T _A = 25°C	1_	±3.5		
Continuous Diam Current (1) = 130 O)	T _A = 70°C	'D	±2.8	Α	
Pulsed Drain Current		I _{DM}	±12		
Continuous Source Current (Diode Conduction) ^{a, b}		Is	-1.6		
M. B. British	T _A = 25°C		1.25	14/	
Maximum Power Dissipation ^{a, b}	T _A = 70°C	P _D	0.8	w	
Operating Junction and Storage Temperature Range	•	T _J , T _{stg}	-55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manifestore Long-Manifestore Anna Anna Language	t ≤ 5 sec			100	0000
Maximum Junction-to-Ambient ^a	Steady State	R_{thJA}	130		°C/W

Notes

a. Surface Mounted on FR4 Board.

b. $t \le 5$ sec.

 $For \ \ SPICE \ model \ information \ via \ the \ Worldwide \ Web: \ \ http://www.vishay.com/www/product/spice.htm$

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Parameter	Symbol	Test Conditions	Limits				
			Min	Тур	Max	Unit	
Static	- 1		•	1	1	•	
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V_{GS} = 0 V, I_D = -10 μA	-12			.,	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-0.45			_ v	
Gate-Body Leakage	I _{GSS}	V_{DS} = 0 V, V_{GS} = ±8 V			±100	nA	
7 0		$V_{DS} = -12 \text{ V}, V_{GS} = 0 \text{ V}$			-1		
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = -12 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^{\circ}\text{C}$			-10	μΑ	
	1.	$V_{DS} \leq$ -5 V, $V_{GS} = -4.5 \text{ V}$	-6				
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \leq$ -5 V, $V_{GS} =$ -2.5 V	-3			Α	
		$V_{GS} = -4.5 \text{ V}, I_D = -3.5 \text{ A}$		0.045	0.055		
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = -2.5 V, I_{D} = -3 A$		0.063	0.075	Ω	
		$V_{GS} = -1.8 \text{ V, } I_{D} = -2 \text{ A}$		0.093	0.118		
Forward Transconductancea	9 _{fs}	$V_{DS} = -5 \text{ V}, I_D = -3.5 \text{ A}$		7		S	
Diode Forward Voltage	V _{SD}	$I_S = -1.6 A, V_{GS} = 0 V$			-1.2	٧	
Dynamic ^b	- '		•	<u>'</u>	1	•	
Total Gate Charge	Qg			9	15	nC	
Gate-Source Charge	Q _{gs}	$V_{DS} = -6 \text{ V}, V_{GS} = -4.5 \text{ V}$ $I_{D} \cong -3.5 \text{ A}$		1.9			
Gate-Drain Charge	Q_{gd}	b		1.5			
Input Capacitance	C _{iss}			1225			
Output Capacitance	C _{oss}	$V_{DS} = -6 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		260		pF	
Reverse Transfer Capacitance	C _{rss}			130			
Switching ^b	<u>'</u>		•	<u>'</u>	1	•	
T On Time	t _{d(on)}			13.0	20		
Turn-On Time	t _r	$V_{DD} = -6 \text{ V, } R_L = 6 \Omega$		15	25	1	
Turn-Off Time	t _{d(off)}	$I_D \cong -1.0 \text{ A}, V_{GEN} = -4.5 \text{ V}$ $R_G = 6 \Omega$		50	70	ns	
	t _f			19	35	1	

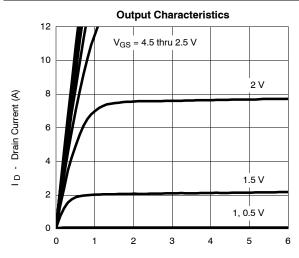
Notes

- a. For DESIGN AID ONLY, not subject to production testing.
 b. Pulse test: PW ≤300 μs duty cycle ≤2%.
 c. Switching time is essentially independent of operating temperature.

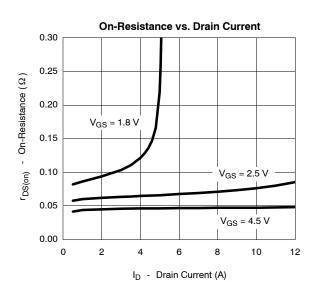


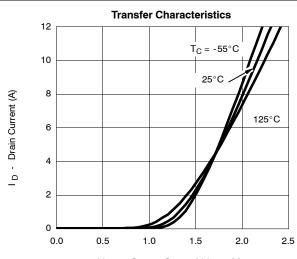


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

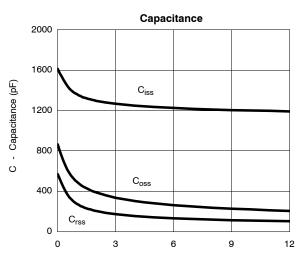


V_{DS} - Drain-to-Source Voltage (V)

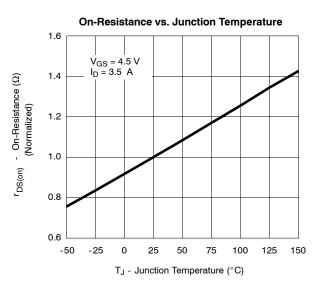




V_{GS} - Gate-to-Source Voltage (V)



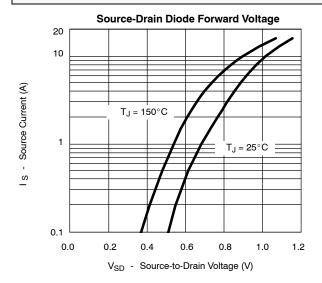
V_{DS} - Drain-to-Source Voltage (V)

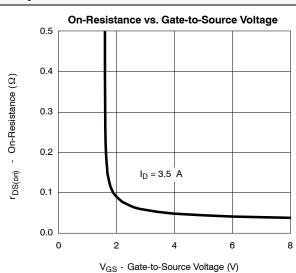


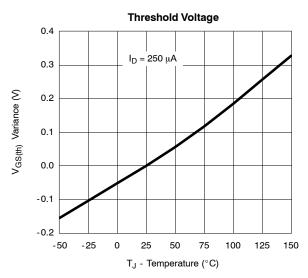
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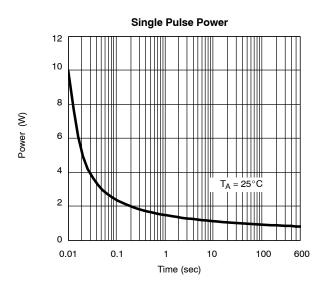


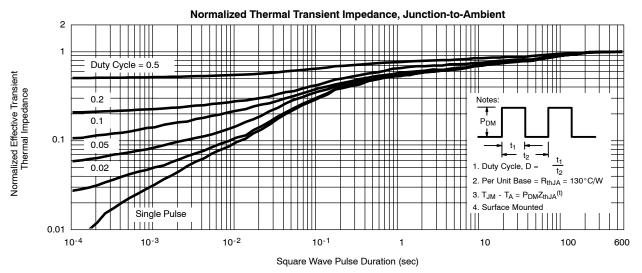
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)













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